Disentangling Orbital and Valley Hall Effects in Bilayers of Transition Metal Dichalcogenides

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The orbital Hall effect (OHE) is the orbital angular momentum analogue of the spin Hall effect (SHE) and refers to the appearance of a transverse orbital angular momentum current after applying a longitudinal electrical field [1]. Recently it has been predicted that the 2H monolayers of transition metal dichalcogenides (TMD) exhibit relatively large orbital Hall conductivity within their semiconducting energy gap, where the spin Hall conductivity vanishes [2,3]. However, since the valley Hall effect (VHE) in these systems also generate a transverse flow of orbital angular momentum, it becomes experimentally challenging to differentiate between these two effects in these materials. The VHE requires an inversion symmetry breaking to occur, and this happens in the monolayer TMD but not into the bilayer. Using density functional theory (DFT) calculations, we demonstrated that a bilayer of 2H-MoS₂ is an orbital Hall insulator that exhibits sizable orbital Hall conductivity signals in their insulating state without SHE and net VHE. Using low-energy models, we further explored the transport properties of these systems. We topologically characterized the orbital Hall insulating phase in TMD monolayers and bilayers using orbital Chern numbers whose values are related to the edge states in nanoribbons. Our results strongly suggest that bilayers of TMDs are highly suitable platforms for direct observation of the orbital Hall insulating phase in two-dimensional materials.

References

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Figures



Figure 1: Schematic representation of the orbital-Hall effect in MoS2.